SISPAD 2006

2006

International Conference on Simulation of Semiconductor Processes and Devices

Monterey, California, USA *6–8 September 2006*

SPONSORED BY IEEE ELECTRON DEVICES SOCIETY

IEEE Catalog Number: **06TH8887**
ISBN: **1-4244-0404-5**

2006 International Conference on Simulation of Semiconductor Process and Devices

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IEEE Catalog Number	06TH8887 (softbound) 06TH8887C (CD ROM)
ISBN	1-4244-0404-5 (softbound) 1-4244-0590-4 (CD ROM)
Library of Congress	2006924884

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